

Title (en)
METHOD FOR THE ORGANISED GROWTH OF NANOSTRUCTURES

Title (de)
VERFAHREN ZUM ORGANISIERTEN WACHSENLASSEN VON NANOSTRUKTUREN

Title (fr)
CROISSANCE ORGANISEE DE NANO-STRUCTURES

Publication
EP 1697559 A1 20060906 (FR)

Application
EP 04816590 A 20041221

Priority
• FR 2004050743 W 20041221
• FR 0351186 A 20031223

Abstract (en)
[origin: FR2864109A1] The procedure consists of forming nucleation sites (4) by irradiating a dielectric substrate (2) with an ion beam giving localised deposition of atoms that form the sites, and then growing the structures on the sites by vapour phase chemical deposition. The substrate can be of silicon or aluminium dioxide or silicon nitride, and the nucleation sites are formed on it with a beam of silicon or germanium ions for growing nano-structures of a semiconductor material with the aid of dichlorosilane or germanium and a gas precursor. The nano-structures formed are three-dimensional with a maximum diameter of 1 - 15 nm, and can be of silicon carbide, diamond, gallium arsenide, nitride or phosphide, or of metal.

IPC 8 full level
C23C 16/04 (2006.01); **B82B 3/00** (2006.01); **C23C 16/02** (2006.01); **H01L 21/20** (2006.01); **H01L 21/205** (2006.01); **H01L 21/265** (2006.01)

CPC (source: EP US)
B82Y 30/00 (2013.01 - EP US); **C23C 16/0272** (2013.01 - EP US); **C23C 16/04** (2013.01 - EP US); **H01L 21/0237** (2013.01 - EP US); **H01L 21/0245** (2013.01 - EP US); **H01L 21/02521** (2013.01 - EP US); **H01L 21/02532** (2013.01 - EP US); **H01L 21/0259** (2013.01 - EP US); **H01L 21/0262** (2013.01 - EP US); **H01L 21/02639** (2013.01 - EP US); **H01L 21/265** (2013.01 - EP US)

Citation (search report)
See references of WO 2005064040A1

Designated contracting state (EPC)
DE FR GB IT

DOCDB simple family (publication)
FR 2864109 A1 20050624; **FR 2864109 B1 20060721**; EP 1697559 A1 20060906; JP 2007517136 A 20070628; US 2007104888 A1 20070510; WO 2005064040 A1 20050714

DOCDB simple family (application)
FR 0351186 A 20031223; EP 04816590 A 20041221; FR 2004050743 W 20041221; JP 2006546284 A 20041221; US 58405304 A 20041221